

L Number	Hits	Search Text	DB	Time stamp
-	607	"Si.sub.x N.sub.y"	USPAT; US-PGPUB	2003/05/13 20:05
-	58366	CVD	USPAT; US-PGPUB	2003/05/13 20:05
-	60364	chemical\$2 adj vapor adj deposit\$3	USPAT; US-PGPUB	2003/05/13 20:06
-	501374	oxide	USPAT; US-PGPUB	2003/05/13 20:06
-	110324	"SiO.sub.2"	USPAT; US-PGPUB	2003/05/13 20:06
-	15864	(CVD or (chemical\$2 adj vapor adj deposit\$3)) near4 (oxide or "SiO.sub.2")	USPAT; US-PGPUB	2003/05/13 20:07
-	10485	BPSG	USPAT; US-PGPUB	2003/05/13 20:07
-	12885	TEOS	USPAT; US-PGPUB	2003/05/13 20:07
-	493	(trench near isolation) and (((thermal\$2 near3 oxid\$5) same ((silicon adj nitride) or "si.sub.3 N.sub.4" or "Si.sub.x N.sub.y") same (((CVD or (chemical\$2 adj vapor adj deposit\$3)) near4 (oxide or "SiO.sub.2")) or BPSG or TEOS))	USPAT; US-PGPUB	2003/05/13 21:10
-	619	atomic adj layer adj deposition	USPAT; US-PGPUB	2003/05/13 21:14
-	267	(atomic adj layer adj deposition) and (((silicon adj nitride) or "si.sub.3 N.sub.4" or "Si.sub.x N.sub.y") and (oxide or "SiO.sub.2"))	USPAT; US-PGPUB	2003/05/13 21:48
-	371	(chemical\$2 adj vapor adj deposit\$3) same (atomic adj layer adj deposition)	USPAT; US-PGPUB	2003/05/13 21:49